PATENT ASSIGNMENT

Electronic Version v1.1
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SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
OERLIKON TRADING AG, TRUEBBACH	01/01/2009

RECEIVING PARTY DATA

Name:	OERLIKON SOLAR IP AG, TRUEBBACH
Street Address:	Hauptstrasse 1a
City:	Truebbach
State/Country:	SWITZERLAND
Postal Code:	CH-9477

PROPERTY NUMBERS Total: 1

Property Type	Number
Application Number:	11691593

OP $40.00 11691593

CORRESPONDENCE DATA

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ATTORNEY DOCKET NUMBER:	H37-091 DIV2
NAME OF SUBMITTER:	Peter C. Michalos, Atty for Applicant

Total Attachments: 14
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OERLIKON TRADING AG, TRÜBBACH
PATENT AND KNOW-HOW ASSIGNMENT AGREEMENT

This PATENT AND KNOW-HOW ASSIGNMENT AGREEMENT (this "Assignment") is made and entered into today with effect as of the 1st day of January 2009 (the "Effective Date") by and between OERLIKON TRADING AG, TRÜBBACH, a corporation organized under the laws of Switzerland ("Assignor"), and OERLIKON SOLAR IP AG, TRÜBBACH, a corporation organized under the laws of Switzerland ("Assignee").

WHEREAS, pursuant to the reorganization of the Oerlikon Solar Business, the parties determined that it would be appropriate and desirable for Assignor to contribute, and for Assignee to receive and assume the Intellectual Property (as defined below) associated with the Oerlikon Solar Business;

WHEREAS, Assignor agrees to assign and transfer to Assignee all of Assignor's right, title and interest in and to the Intellectual Property (as defined below);

WHEREAS, Assignor is the owner of the patents and patent applications set forth on Schedule 1 hereto, including all continuations, reissues, reexaminations, registrations, renewals, and extensions thereof (the "Patents") as well as the product- and production related know-how related to the Oerlikon Solar Business (the "Know-How"; collectively the "Intellectual Property"); and

WHEREAS, Assignee desires to get assigned all of Assignor's right, title and interest in and to the Intellectual Property.

NOW THEREFORE, in consideration of CHF [redacted] the "Consideration"), the parties agree as follows:

1. As of the Effective Date, 2009, Assignor hereby sells, assigns and transfers to Assignee and Assignee hereby purchases, and accepts assignment and transfer of, all of Assignor's right, title and interest in and to the Intellectual Property. The Consideration shall be payable by Assignee within 14 days from signing of this Assignment. Upon receipt by Assignor of the Consideration all royalties due to Assignor under the License Agreements (as defined below) as from January 1st, 2009 shall belong and shall be assigned to Assignee or shall, to the extent already paid by the Licensees (as defined below) to the Assignor, be remitted by the Assignor to the Assignee forthwith.

2. Assignor hereby represents and warrants to Assignee that:

(a) Save for the license rights granted by Licensor to licensees (the "Licensees") under the license agreements identified in Schedule 2 (the "License Agreements"), Assignor is the owner of the entire right, title and interest in and to the Intellectual Property free and clear of all liens, claims and encumbrances; and

(b) Assignor has the requisite legal and corporate power and authority to enter into this Assignment and there are no outstanding assignments, grants, licenses, encumbrances, obligations or agreements, whether written, oral or implied, that are inconsistent with this Intellectual Property Assignment.

Assignee acknowledges and accepts Licensees' rights in and to the Licensed Intellectual Property, Licensed Products and Improvements as defined in, and in accordance with the terms of, the License Agreements. Assignee further acknowledges and accepts that part of the Intellectual Property is not yet registered in the relevant registers in the name of Assignor and that Assignee will not hold Assignor liable in case applicable laws have the effect that Assignor does not or will not acquire ownership over such Intellectual Property.

3. Except as expressly set forth herein, Assignor makes no warranties, express or implied, with respect to the Intellectual Property.

4. Assignee acknowledges and accepts the content of the License Agreements and agrees that the License Agreements shall continue to remain in full force and effect. To this end, Assignee shall enter into the required transfer agreements with Assignor, as well as OC Oerlikon Balzers AG, Iramali 18, FL-9496 Balzers, Liechtenstein, and Oerlikon Solar AG, Trübbach, Hauptstrasse 1a, CH-9477 Trübbach, respectively.

5. Subject to Clause 2, Assignor hereby covenants that Assignor shall, upon reasonable request of Assignee and at the cost and expense of Assignee, take all actions and execute all documents necessary or desirable to perfect the interest of Assignee in and to the Intellectual Property and shall not enter into any agreement in conflict with this Assignment.

6. This Assignment may be executed in one or more counterparts, each of which when executed shall be deemed to be an original but all of which taken together shall constitute one and the same agreement.

7. This Assignment shall be interpreted and governed in accordance with the laws of Switzerland, regardless of the laws that might otherwise govern under principles of conflicts of laws applicable thereto. All actions and proceedings arising out of or relating to this Assignment shall be heard and determined by Swiss courts.

8. Assignee acknowledges and agrees that it shall have no rights in and to any trademarks and service marks as well as any copyrights of the Assignor and that no such trademarks and service marks and/or copyrights are assigned hereunder to Assignee. Assignee covenants that it shall not use any of the Assignor's trademarks, service marks and/or copyrights, in particular, that it shall not use any trademarks, service marks or similar designations alone or in combination with any trademark, service mark or trade name proprietary to Assignee.

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OERLIKON TRADING AG, TRÜBBACH

By: _____

Name: Erich Haefeli — Jörg Baur

Title: Managing Director — Senior Patent Counsel

Date: April 17, 2009 — April 17, 2009

OERLIKON SOLAR IP AG, TRÜBBACH

By: _____

Name: Björn Bajan — Wolfgang Niggli

Title: Board Member — Board Member

Date: April 22, 2009 — April 21, 2009

SCHEDULE 1

Patents and Patent Applications

Applications and Patents SOLAR

PR-No.	Country	Appl.Date	Appl. No.	Grant.Date	Patent No.	Title
19 8937.0	EP: CH, DE, FR, GB	05.04.1991	91105383.3	27.12.1995	0452745	CVD; Reaktor; Gasführung
19 8937.0.1 CON	US	25.05.1993	08/067392	06.06.1995	5422139	
SO 91/1	FR	29.05.1991	9106478	24.12.1993	2677043	PCVD; Plasmabox; Hochfrequenzeinkoppelung; KAI-Anlage
SO 91/1	JP	29.05.1992	161876/92	27.04.2001	3182702	
19 9108.0	EP: CH, DE, FR, GB	09.09.1992	92115397.9	29.12.1999	0533044	Plasmapolymerisation; Mittelfrequenz; Pulsen
19 9108.0	JP	21.09.1992	4-251329	07.03.2003	3406619	
19 9108.0	US	18.09.1992	947709	29.03.1994	5298290	
19 9108.0.1 DIV	US	19.11.1993	08/154946	11.04.1995	5405448	
19 9222.0	EP: CH, DE, GB	29.11.1993	93119165.4	25.09.1996	603587	Magnetfeldanordnung für Magnetron mit grossflächiger Targeterosion; ScanMag
19 9222.0	JP	14.12.1993	5-313369	18.06.2004	3566327	
19 9222.0	US	16.11.1993	08/153608	21.03.1995	5399253	
19 9301.0	CH	03.05.1993	1344/93-0	15.04.1997	687987	Parallel Processing Production System for PECVD
19 9301.0	DE	14.04.1994	4412902.5	08.02.2007	4412902	
19 9301.0	FR	02.05.1994	9405316	08.08.1997	2705104	
19 9301.0	JP	06.05.1994	6-94375	03.06.2005	3683599	
19 9301.0	US	03.06.1994	08/237432	02.12.1997	5693238	
19 9301.0.1 DIV	DE	14.04.1994	4447977.8	-	-	
19 9301.0.1.1	TW	21.10.1999	88118227	06.03.2002	NI144307	
19 9301.0.1.1 CIP	US	23.10.1998	09/177894	02.10.2001	6296735	
19 9301.0.1.1 CON	US	24.08.1999	09/379742	18.03.2003	6533534	
19 9301.0.1.1 DIV	US	10.08.2001	09/925646	06.01.2004	6673255	
19 9302.0	CH	03.05.1993	1343/93-8	15.04.1997	687986	Method for Parallel Process in Production System for PECVD; KAI-Prozess
19 9302.0	DE	14.04.1994	4412915.7	15.12.2005	4412915	
19 9302.0	FR	02.05.1994	9405315	30.04.1997	2705165	
19 9302.0	JP	06.05.1994	6-94470	22.10.2004	3609448	
19 9302.0	US	03.05.1994	08/237575	14.05.1996	5515986	
19 9302.0.1 DIV	JP	06.05.1994	2004-238129	21.12.2007	4057568	
LS 94/2	DE(2)	26.07.1995	19527246.3	-	-	Heizbarer Schwenktisch
LS 94/2	JP(1)	26.07.1995	1995-190884	06.06.2008	4131523	
19 9415.0	FR	20.10.1995	9512381	10.04.1998	2728725	Heizbare Elektrode
19 9415.0	US	21.12.1995	08/576236	22.12.1998	5852275	
19 9416.0	CH	17.10.1995	02937/95	13.07.2001	691376	Beschichtungssystem
19 9416.0	KR	16.10.1996	96-46173	17.06.2004	0437752	
19 9416.0	US	08.08.1996	08/693987	12.08.1997	5655277	
19 9506.0	US	15.12.1995	08/573257	04.08.1998	5789851	Field emission display; Resistive layer
19 9613.0 AP	CH	15.10.1996	2516/96	14.09.2001	691680	Magnetgestütztes Transportsystem für Vakuumbeschichtungsanlage
19 9613.0 AP	US	26.09.1997	08/939027	08.06.1999	5909995	

PR-No.	Country	Appl.Date	Appl. No.	Grant.Date	Patent No.	Title
19 9701.0	PCT/EP: DE, ES, FR, GB, IT, NL	13.01.1998	98900039.3	29.03.2006	0953204	Plasmareaktor für grosse Flächen mit Elektrodenarray
19 9701.0	PCT/JP	13.01.1998	534036/1998	-	-	
19 9701.0	PCT/KR	13.01.1998	99-7006493	18.10.2005	0523766	
19 9701.0	TW	02.02.1998	87101169	02.07.2001	NI128300	
19 9701.0	US	17.01.1997	08/784578	09.11.1999	5981899	
19 9701.0.1 CIP	US	23.07.1999	09/360247	28.08.2001	6281469	
19 9706.0	CH	08.07.1997	1653/97	15.10.2002	692741	Batch Vakuum Prozess-System mit Zentral-Handler
19 9706.0	JP	07.07.1998	191583/1998	-	-	
19 9706.0	KR	07.07.1998	98-27338	27.01.2006	0549455	
19 9706.0	TW	06.07.1998	87110892	24.09.2004	NI202733	
19 9706.0.1 CON	US	17.11.1999	09/441374	21.05.2002	6391377	
19 9706.0.1.1 CON	US	17.11.1999	09/441373	23.01.2001	6177129	
19 9706.0.1.1.1 CON	US	23.01.2001	09/766835	10.05.2005	6890862	
19 9707.0	JP	23.06.1998	175940/1998	-	-	Flow control system; Gaseinlasssystem
19 9707.0	KR	23.06.1998	98-23577	25.10.2005	0525353	
19 9707.0	US	24.06.1997	08/881759	13.06.2000	6074691	
19 9723.0	CH	17.12.1997	2897/97	-	-	Grossflächen-Magnetron; Scanmag; BigMag
19 9723.0	HK	08.06.2001	01103956.5	18.08.2006	1033344	
19 9723.0	PCT/CN	15.12.1998	98812383.5	01.02.2006	98812383.5	
19 9723.0	PCT/EP	15.12.1998	98958140.0	-	-	
19 9723.0	PCT/JP	15.12.1998	539185/2000	21.04.2006	3794919	
19 9723.0	PCT/KR	15.12.1998	2000-7005767	25.04.2005	0487059	
19 9723.0	TW	24.12.1998	87120993	05.06.2002	NI127546	
19 9723.0	US	19.02.1998	09/026446	25.07.2000	6093293	
19 9723.0 DIV3	PCT/KR	15.12.1998	2008-7030780	-	-	
19 9723.0.1 DIV	PCT/CN	15.12.1998	200510128582.2	-	-	
19 9723.0.1 DIV	PCT/JP	15.12.1998	316819/2003	-	-	
19 9723.0.1 DIV	PCT/KR	15.12.1998	2004-7007791	29.08.2005	0512523	
19 9723.0.1 DIV	US	05.06.2000	09/587543	04.09.2001	6284106	
19 9723.0.1.1 CIP	US	06.09.2002	10/236636	20.01.2004	6679977	
19 9723.0.1.1 DIV	PCT/CN	15.12.1998	200610101618.2	-	-	
19 9723.0.1.1 DIV	PCT/KR	15.12.1998	2005-7002165	-	-	
19 9723.0.1.1 DIV	US	25.06.2001	09/888923	24.09.2002	6454920	
19 9802.0	CH	04.02.1998	0273/98	15.11.2002	692821	Kammertrennventil beidseitig dichtend
19 9802.0	PCT/JP	27.01.1999	530725/2000	-	-	
19 9802.0	PCT/US	27.01.1999	09/632847	06.08.2002	6427973	
19 9804.0	PCT/EP: CH, DE	09.06.1999	99923361.2	18.09.2002	1089949	Schnellheizanordnung für grossflächige Substrate
19 9804.0	PCT/JP	09.06.1999	557206/2000	-	-	
19 9804.0	PCT/KR	09.06.1999	2000-7014755	29.08.2006	0620444	

PR-No.	Country	Appl.Date	Appl. No.	Grant.Date	Patent No.	Title
19 9804.0.1 CIP	US	12.01.2000	09/481392	04.02.2003	6513347	
19 9808.0	DE	28.04.1999	19919384.3	-	-	Plasma Etch Cleaning and Related Processes
19 9808.0	FR	28.04.1999	9905375	30.07.2004	2777913	
19 9808.0	GB	28.04.1999	9909805.5	09.01.2002	2339553	
19 9808.0	JP	27.04.1999	120190/1999	-	-	
19 9808.0	KR	28.04.1999	99-15266	03.05.2007	0716806	
19 9808.0	TW	01.06.1998	87108516	26.11.2001	NI137790	
19 9808.0	US	28.04.1998	09/066978	03.10.2000	6127271	
19 9823.0	CH	29.04.1999	00794/99	15.06.2005	694699	Hohe Raten für Si u.a. thermodynamisch stabile Schichten
19 9823.0	HK	22.08.2002	02106186.9	05.08.2005	HK1044571	
19 9823.0	PCT/EP; DE, FR, GB	11.04.2000	00914006.2	05.01.2005	1187945	
19 9823.0	PCT/JP	11.04.2000	615426/2000	-	-	
19 9823.0	PCT/US	11.04.2000	10/031258	03.02.2004	6685994	
19 9823.0	TW	20.04.2000	89107450	04.03.2003	NI164965	
19 9910.0	CH	10.08.1999	1466/99	-	-	Reactor design for uniform RF plasma treatment on large size substrate
19 9910.0	HK	19.11.2002	02108376.5	-	-	
19 9910.0	PCT/EP	08.08.2000	00947729.0	-	-	
19 9910.0	PCT/JP	08.08.2000	516221/2001	-	-	
19 9910.0	PCT/KR	08.08.2000	2002-7001426	31.12.2007	0792314	
19 9910.0	TW	07.08.2000	89115856	26.06.2002	NI151505	
19 9910.0	US	22.09.1999	09/401158	08.05.2001	6228438	
19 9910.0 DIV1	PCT/EP	23.02.2009	09002513.1	-	-	
19 9910.0 DIV2	US	22.09.1999	11/691593	-	-	
19 9910.0 DIV3	US	22.09.1999	11/872957	-	-	
19 9911.0 AP	PCT/EP; AT, CH, DE, FR, GB, NL	29.08.2000	00953372.0	31.01.2007	1221175	Arc-Unterdrückung für Sputterprozesse
19 9911.0 AP	PCT/JP	29.08.2000	530893/2001	-	-	
19 9911.0 AP	PCT/KR	29.08.2000	2002-7004065	17.01.2008	0797736	
19 9911.0 AP	PCT/US	29.08.2000	10/108666	25.05.2004	6740207	
19 9911.0 AP	TW	12.10.2000	89121301	10.09.2002	NI155771	
19 9915.0	CN	26.04.2001	01117251.7	22.12.2004	ZL01117251.7	Plasmareaktor; Gaseinlasssystem; binärer Baum
19 9915.0	DE	23.04.2001	10119766.7	26.02.2009	10119766	
19 9915.0	FR	26.04.2001	0105619	07.01.2005	2808224	
19 9915.0	JP	25.04.2001	127862/2001	-	-	
19 9915.0	KR	26.04.2001	2001-22656	30.07.2007	0746439	
19 9915.0	TW	25.04.2001	90109755	21.02.2003	164383	
19 9915.0	US	26.04.2000	09/559408	07.01.2003	6502530	
19 9915.0 DIV1	DE	23.04.2001	10165956.6	-	-	
19 9915.0 DIV2	US	23.10.2007	11/877419	-	-	
19 9915.0.1 DIV	CN	26.04.2001	200410088066.7	01.08.2007	1330219	

PR-No.	Country	Appl.Date	Appl. No.	Grant.Date	Patent No.	Title
19 9915.0.1.1 CON	US	21.11.2002	10/300873	11.12.2007	7306829	

PR-No.	Country	Appl.Date	Appl. No.	Grant.Date	Patent No.	Title
20 0110.0	HK	19.11.2004	04109166.5	14.09.2007	HK1066323	Slim Pins; Lifting and/or holding pins for large substrates
20 0110.0	PCT/CN	15.07.2002	02814381.7	31.01.2007	1298017	
20 0110.0	PCT/EP; AT, BE, CH, CZ, DE, ES, FI, FR, GB, GR, IT, NL, SE, TR	15.07.2002	02767211.2	13.06.2007	1435106	
20 0110.0	PCT/JP	15.07.2002	2003-513889	-	-	
20 0110.0	PCT/KR	15.07.2002	2004-7000758	-	-	
20 0110.0	PCT/US	15.07.2002	10/484174	-	-	
20 0110.0	TW	15.07.2002	91115688	06.08.2004	224842	
20 0208.2	PCT/CN	22.10.2003	200380101537.7	-	-	Method for producing Boron doped semiconductors
20 0208.2	PCT/EP	22.10.2003	03750232.5	-	-	
20 0208.2	PCT/IN	22.10.2003	00207/MUMNP/2005	19.06.2006	202725	
20 0208.2	PCT/JP	22.10.2003	2005-501493	-	-	
20 0208.2	PCT/KR	22.10.2003	10-2005-7006591	-	-	
20 0208.2	US	22.10.2003	10/691102	18.03.2008	7344909	
20 0208.2 DIV1	US	22.10.2003	11/947245	17.03.2009	7504279	
20 0208.2 DIV2	US	22.10.2003	12/361020	-	-	
20 0213.0	PCT/CN	12.11.2003	200380103273.9	-	-	Generation 6 Kai-concept; Anlagenkonfiguration
20 0213.0	PCT/EP	12.11.2003	03769143.3	-	-	
20 0213.0	PCT/KR	12.11.2003	2005-7008231	-	-	
20 0213.0	US	14.11.2003	10/713339	17.07.2007	7244086	
20 0213.0 DIV1	US	14.11.2003	11/755423	-	-	
20 0311.0	PCT/CN	26.07.2004	200480021464.5	-	-	Sliding anode; Sputter deposition process for large area deposition
20 0311.0	PCT/EP	26.07.2004	04738112.4	-	-	
20 0311.0	PCT/JP	26.07.2004	520649/2006	-	-	
20 0311.0	PCT/KR	26.07.2004	2006-7001708	-	-	
20 0311.0	TW	26.07.2004	93122325	-	-	
20 0311.0	US/A	23.07.2004	10/912365	-	-	
20 0312.0	PCT/CN	26.07.2004	200480022057.6	-	-	Etch-Cleaning method for increasing plasma processing equipment throughput
20 0312.0	PCT/EP	26.07.2004	04738110.8	-	-	
20 0312.0	PCT/JP	26.07.2004	521364/2006	-	-	
20 0312.0	PCT/KR	26.07.2004	2006-7001984	-	-	
20 0312.0	TW	28.07.2004	93122484	-	-	
20 0312.0	US/A	23.07.2004	10/898458	-	-	
20 0316.1	PCT/CN	08.09.2004	200480032865.0	-	-	Lens rectangular; Electrode design for large area substrate
20 0316.1	PCT/EP: CH, DE, ES, FI, FR, GB, IT, SE, TR	08.09.2004	04761903.6	13.06.2007	1665323	
20 0316.1	PCT/IN	08.09.2004	1132/DELNP/2006	-	-	
20 0316.1	PCT/JP	08.09.2004	525597/2006	-	-	
20 0316.1	PCT/KR	08.09.2004	2006-7005300	-	-	

PR-No.	Country	Appl.Date	Appl. No.	Grant.Date	Patent No.	Title
20 0316.1	TW	09.09.2004	93127228	-	-	
20 0316.1	US/A	08.09.2004	10/935779	10.02.2009	7487740	
20 0316.1 CON	US/A	08.09.2004	12/346917	-	-	
20 0402.0	TW	02.02.2005	94103194	-	-	Backcontact and backreflector for thin film silicon solar cells; light-trapping; white layer
20 0403.0	CH	30.04.2004	0761/04	-	-	Compensating Dielectric Layer combined with Gas shower; Top lens
20 0403.0	PCT/CN	14.03.2005	200580013677.8	-	-	
20 0403.0	PCT/EP	14.03.2005	05714692.0	-	-	
20 0403.0	PCT/IN	14.03.2005	3523/KOLNP/2006	-	-	
20 0403.0	PCT/JP	14.03.2005	509846/2007	-	-	
20 0403.0	PCT/KR	14.03.2005	2006-7021865	-	-	
20 0403.0	TW	15.04.2005	94111952	-	-	
20 0403.0	US	30.04.2004	10/835708	11.11.2008	7449220	
20 0403.0 DIV1	US	30.04.2004	12/235845	-	-	
20 0404.0	PCT/CN	16.02.2005	200580005287.6	-	-	Diffusion barrier layer and method for manufacturing it; encapsulation; multiple inorganic layer system
20 0404.0	PCT/EP	16.02.2005	05706511.2	-	-	
20 0404.0	PCT/JP	16.02.2005	553410/2006	-	-	
20 0404.0	TW	18.02.2005	94104751	-	-	
20 0404.0	US	18.02.2005	11/061143	17.02.2009	7492091	
20 0404.0 CON	US	18.02.2005	12/330903	-	-	
20 0408.0	CH	03.06.2004	935/04	-	-	Laserscribing; Luftlagerung; Substrathandling
20 0408.0	PCT/BR	27.05.2005	PI0511797-6	-	-	
20 0408.0	PCT/CN	27.05.2005	200580017793.7	-	-	
20 0408.0	PCT/EP	27.05.2005	05742263.6	-	-	
20 0408.0	PCT/IL	27.05.2005	179554	-	-	
20 0408.0	PCT/IN	27.05.2005		-	-	
20 0408.0	PCT/JP	27.05.2005	2007/513651	-	-	
20 0408.0	PCT/KR	27.05.2005	2007-7000126	-	-	
20 0408.0	PCT/US	27.05.2005	11/597856	-	-	
20 0416.0	US	31.05.2005	11/141620	-	-	UV Laserscribing
20 0417.0	PCT/EP: DE, ES, FR, GB, IT	26.05.2005	05742317.0	28.05.2008	1754254	Pins; lifting device; KAI
20 0417.0	PCT/JP	26.05.2005	513650/2007	-	-	
20 0417.0	PCT/KR	26.05.2005	2006-7027409	-	-	
20 0417.0	TW	27.05.2005	94117365	-	-	
20 0417.0	US	15.05.2005	11/137230	-	-	
20 0421.0	PCT/AU	07.07.2005	2005262191	-	-	Air bearing; large substrate; transport mechanism
20 0421.0	PCT/CN	07.07.2005	200580023248.9	-	-	
20 0421.0	PCT/EP	07.07.2005	05756159.9	-	-	
20 0421.0	PCT/IL	07.07.2005	180080	-	-	

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20 0421.0	PCT/JP	07.07.2005	519595/2007	-	-	
20 0421.0	PCT/KR	07.07.2005	2007-7000087	-	-	
20 0421.0	PCT/US	07.07.2005	11/571604	-	-	
20 0421.0	PCT/US/A	07.07.2005	11/571604	-	-	
20 0421.0	TW	08.07.2005	94123153	-	-	
20 0425.0	PCT/EP	28.07.2005	05762954.5	-	-	Adhesion layer; microcrystalline silicon; PECVD
20 0425.0	PCT/US	28.07.2005	11/573162	-	-	
20 0425.0	TW	03.08.2005	94126299	-	-	
20 0429.0	PCT/AU	11.11.2005	2005304253	-	-	KAI PECVD; RF Matching; impedance
20 0429.0	PCT/CN	11.11.2005	200580038684.3	-	-	
20 0429.0	PCT/EP	11.11.2005	05801054.7	-	-	
20 0429.0	PCT/JP	11.11.2005	540474/2007	-	-	
20 0429.0	PCT/KR	11.11.2005	10-2007-7007856	-	-	
20 0429.0	PCT/SG	11.11.2005	200703366-5	-	-	
20 0429.0	PCT/US	11.11.2005	11/719115	-	-	
20 0429.0	TW	14.11.2005	94139874	-	-	
20 0431.0	PCT/AU	23.11.2005	2005309226	-	-	KAI 3000 concept; inverted shoe box; plasma processing; compensation means for deviation of flatness
20 0431.0	PCT/CN	23.11.2005	200580039880.2	-	-	
20 0431.0	PCT/EP; DE, ES, FR, GB, IT, NL	23.11.2005	05803234.3	02.04.2008	1815493	
20 0431.0	PCT/JP	23.11.2005	541632/2007	-	-	
20 0431.0	PCT/KR	23.11.2005	10-2007-7007616	-	-	
20 0431.0	PCT/SG	23.11.2005	200703757-5	-	-	
20 0431.0	PCT/US	23.11.2005	11/720034	-	-	
20 0431.0 DIV1	PCT/EP	23.11.2005	08005612.0	-	-	
20 0432.0	PCT/EP	16.12.2005	05815646.4	-	-	Moving magnet system; big mag; diamond magnetron; large area sputter system
20 0432.0	PCT/JP	16.12.2005	545810/2007	-	-	
20 0432.0	PCT/US	16.12.2005	11/577576	-	-	
20 0432.0	TW	16.12.2005	94144592	-	-	
20 0508.0	PCT/CN	10.04.2006	200680011479.2	-	-	Solar cell; encapsulation
20 0508.0	PCT/EP	10.04.2006	06721903.0	-	-	
20 0508.0	PCT/JP	10.04.2006	2008-504602	-	-	
20 0508.0	PCT/KR	10.04.2006	2007-7022953	-	-	
20 0508.0	US	10.04.2006	11/279152	-	-	
20 0518.0	PCT/CN	28.06.2006	200680023110.3	-	-	Precoating; microcristalline silicon
20 0518.0	PCT/EP	28.06.2006	06763956.7	-	-	
20 0518.0	PCT/JP	28.06.2006	518843/2008	-	-	
20 0518.0	US	28.06.2006	11/427048	-	-	
20 0518.0 DIV1	US	28.06.2006	12/372813	-	-	
20 0524.0	PCT/CN	13.10.2006	200680038561.4	-	-	Remote plasma source; gas distribution; spider web

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20 0524.0	PCT/EP	13.10.2006	06804806.5	-	-	
20 0524.0	PCT/JP	13.10.2006	2008-535865	-	-	
20 0524.0	PCT/KR	13.10.2006	2008-7009009	-	-	
20 0524.0	PCT/SG	13.10.2006	200802326-9	-	-	
20 0524.0	US	16.10.2006	11/549679	-	-	
20 0528.0	PCT/CN	12.12.2006	200680052469.3	-	-	Improved target utilization; big mag; target edge movement
20 0528.0	PCT/EP	12.12.2006	06817742.7	-	-	
20 0528.0	PCT/IN	12.12.2006	5042/DELNP/2008	-	-	
20 0528.0	PCT/JP	12.12.2006	544730/2008	-	-	
20 0528.0	PCT/KR	12.12.2006	2008-7017014	-	-	
20 0528.0	PCT/SG	12.12.2006	200804421-6	-	-	
20 0528.0	US	13.12.2006	11/638176	-	-	
20 0530.0	PCT/CN	20.12.2006	200680048479.X	-	-	ScanMag with spiral magnet arrangement; snake
20 0530.0	PCT/EP	20.12.2006	06830754.5	-	-	
20 0530.0	PCT/IN	20.12.2006	2280/KOLNP/2008	-	-	
20 0530.0	PCT/JP	20.12.2006	546443/2008	-	-	
20 0530.0	PCT/KR	20.12.2006	2008-7017866	-	-	
20 0530.0	PCT/SG	20.12.2006	200804100-6	-	-	
20 0530.0	US	22.12.2006	11/615268	-	-	
20 0703.0	PCT	29.02.2008	2008/000080	-	-	Inline system; TCO; Heiztisch; LPCVD
20 0703.0	TW	03.03.2008	097107308	-	-	
20 0703.0	US	29.02.2008	12/040292	-	-	
20 0712.1	PCT	18.04.2008	2008/054762	-	-	Solar panel; test equipment; shunt detection
20 0712.1	TW	21.04.2008	97114443	-	-	
20 0712.1	US	18.04.2008	12/105331	-	-	
20 0721.0	PCT	28.08.2008	2008/061316	-	-	Laser spot; Laser scribing
20 0721.0	TW	29.08.2008	97113101	-	-	
20 0724.0	PCT	16.09.2008	2008/000385	-	-	Modified dielectic lens; muc-Si; micromroph
20 0724.0	TW	24.11.2008	097136595	-	-	
20 0728.0	PCT	18.12.2008	2008/067936	-	-	TCO interlayer; textured substrate
20 0728.0	TW	19.12.2008	097149853	-	-	
20 0733.0	PCT	19.12.2008	2008/010909	-	-	Gate valve
20 0733.0	TW	15.12.2008	097148735	-	-	
20 0742.0	PCT	19.12.2008	2008/068020	-	-	PECVD; Multielectrode
20 0742.0	TW	19.12.2008	097149766	-	-	
20 0743.0	PCT	13.01.2009	2009/050327	-	-	Contact stripes; induction coil; electrical contact
20 0743.0	TW	14.01.2009	98101200	-	-	
20 0759.0	PCT	29.02.2008	2008/001634	-	-	Referenzsolarzelle
20 0801.0	PCT	04.02.2009	2009/051288	-	-	DLC für Solarzellen
20 0801.0	TW	16.02.2009	098105190	-	-	

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20 0802.0 PRO	US	18.04.2008	61/046115	-	-	Super line; thin film; solar modules
20 0808.0 PRO	US	02.05.2008	61/049899	-	-	Plasma processing; ground plate
20 0813.0 PRO	US	09.07.2008	61/079286	-	-	Remote plasma cleaning method and apparatus
20 0815.0 PRO	US	05.11.2008	61/111443	-	-	TiO2; intermediate layer
20 0816.0 PRO	US	01.10.2008	61/101736	-	-	Segmentierte Linse
20 0817.0 PRO	US	18.04.2008	61/046090	-	-	Microcrystalline; amorphous silicon film; photovoltaic device
20 0818.0 PRO	US	18.04.2008	61/046103	-	-	Microcrystalline; amorphous silicon film; photovoltaic device
20 0822.0	PCT	18.06.2008	2008/057716	-	-	Photovoltaic cells; converter panel
20 0822.0	TW	-	-	-	-	
20 0822.0 PRO	US	18.06.2008	61/073515	-	-	
20 0824.0 PRO	US	19.08.2008	61/089925	-	-	Hot-trap; unreacted gas; catalytical active surfaces
20 0825.0 PRO	US	17.07.2008	61/081472	-	-	Cover for transport roller; vacuum deposition system
20 0827.0 PRO	US	29.10.2008	61/109290	-	-	Unsharp; edge round; rounded corners
20 0828.0 PRO	US	29.10.2008	61/109280	-	-	Multiple laser scribes
20 0829.0 PRO	US	19.08.2008	61/089931	-	-	Electrical and optical properties of silicon solar cells
20 0830.0 PRO	US	19.08.2008	61/089934	-	-	Silicon solar cells; TCO
20 0832.0 PRO	US	01.08.2008	61/085470	-	-	Photovoltaic cell production
20 0834.0 PRO	US	29.08.2008	61/092963	-	-	Vacuum system
20 0835.0 PRO	US	19.01.2009	61/145613	-	-	Verbindungsstück; Vakuumverbindung
20 0839.0 PRO	US	07.10.2008	61/103293	-	-	Process for laminating photovoltaic cell
20 0840.0 PRO	US	23.09.2008	61/099340	-	-	Trapping unreacted gas; hot trap
20 0845.0 PRO	US	29.08.2008	61/092949	-	-	Depositing an amorphous silicon film; photovoltaic devices
20 0845.1 PRO	US	01.09.2008	61/093418	-	-	Thin film solar PV
20 0845.2 PRO	US	01.09.2008	61/093420	-	-	LPCVD-ZNO TCO; P-I-N Amorphous silicon; micromorph;
20 0846.0 PRO	US	01.09.2008	61/093423	-	-	TCO 1200; oxide thin films
20 0846.1 PRO	US	01.09.2008	61/093424	-	-	LPCVD ZNO layers by TCO
20 0849.0 PRO	US	23.09.2008	61/099337	-	-	Fabricating a photovoltaic panel
20 0851.0 PRO	US	21.03.2008	61/038553	-	-	Solar cells; thin film
20 0851.1 PRO	US	20.02.2009	61/154160	-	-	Swiss cheese; TCO structure
20 0852.0	DE	08.08.2008	102008037058.4	-	-	Leckrate einer Vakuumanlage; Lecksuche
20 0853.0	DE	28.10.2008	102008053522.2	-	-	Verfahren zum Reinigen einer Vakuumpumpe
20 0864.0 PRO	US	31.10.2008	61/110070	-	-	Liquid precursor disposal
20 0865.0 PRO	US	31.10.2008	61/110076	-	-	Liquid precursor; recycle and disposal
20 0867.0 PRO	US	24.11.2008	61/117349	-	-	Method for improving light trapping of series connected thin film solar cell devices
20 0868.0 PRO	US	24.11.2008	61/117340	-	-	Method for fixing and supporting photovoltaic modules
20 0902.0 PRO	US	19.01.2009	61/145614	-	-	Light management; thin film silicon solar cells
20 0903.0 PRO	US	21.01.2009	61/146807	-	-	Tin side; fire side; glass side selection

SCHEDULE 2

"Oerlikon License Agreement"

and

"Technology License Agreement"